

**Amendments to the Specification:**

Page 7, please replace Paragraph 4 with the following paragraph:

~~FIG. 8 shows~~ FIGS. 8(A)-8(B) show another schematically drawn apparatus used in Example 4, used for processing (impurity-doping) semiconductors;

Page 7, please replace Paragraph 6 with the following paragraph:

~~FIG. 10 shows~~ FIGS. 10(A)-10(C) show schematically the steps of a process for fabricating a TFT as in Example 5;

Page 7, please replace Paragraph 7 with the following paragraph:

~~FIG. 11 shows~~ FIGS. 11(A)-(E) show schematically the steps of a process for fabricating a TFT as in Examples 6 and 7;

Page 7, please replace Paragraph 8 with the following paragraph:

~~FIG. 12 is a graph~~ FIGS. 12(A)-(C) are graphs showing the C-V characteristics of a TFT having fabricated in an Example;

Page 7, please replace Paragraph 11 with the following paragraph:

~~FIG. 16 gives~~ FIGS. 16(A)-(B) give the characteristic curves for an inverter and a ring oscillator having fabricated by a process according to the present invention.